1. General description

NPN high-voltage low V_{CEsat} transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9215Z-Q

2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- Medium power SMD plastic package
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- LED driver for LED chain module
- LCD backlighting
- · Automotive motor management
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	150	V
I _C	collector current		-	-	2	Α
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 100 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	100	240	-	



150 V, 2 A NPN high-voltage low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C; C
2	С	collector		в
3	Е	emitter		
4	С	collector	1 2 3	Ė
			SC-73 (SOT223)	sym016

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PBHV8215Z-Q	SC-73	plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223				

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV8215Z-Q	V8215Z

150 V, 2 A NPN high-voltage low VCEsat transistor

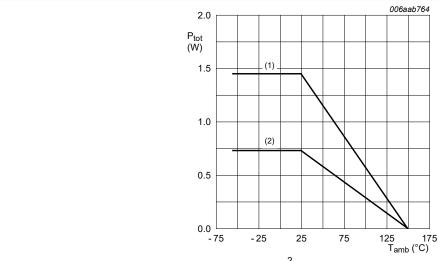
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	350	V
V_{CEO}	collector-emitter voltage	open base		-	150	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	4	Α
I _{BM}	peak base current			-	500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.45	W
			[2]	-	0.73	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm 2 . Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

Power derating curves

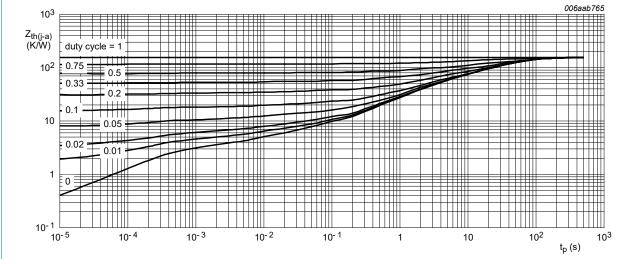
150 V, 2 A NPN high-voltage low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

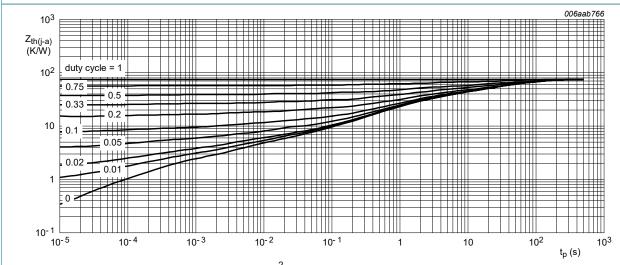
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	85	K/W
jun	junction to ambient		[2]	-	-	170	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

150 V, 2 A NPN high-voltage low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 120 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 120 V; I _E = 0 A; T _j = 150 °C	-	-	10	μΑ
I _{ЕВО}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
CES	collector-emitter cut-off current	V _{CE} = 120 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 100 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	100	240	-	
		V_{CE} = 10 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	230	-	
		V_{CE} = 10 V; I_{C} = 1.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	90	210	-	
		V_{CE} = 10 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	55	130	-	
V _{CEsat} collector-emitter saturation voltage	collector-emitter saturation voltage	I_C = 100 mA; I_B = 20 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	15	30	mV
		I_C = 1 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	90	170	mV
		I_C = 1.5 A; I_B = 300 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	130	220	mV
		$I_C = 2 \text{ A}$; $I_B = 400 \text{ mA}$; pulsed; $t_p \le$	-	170	280	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	85	140	mΩ
V _{BEsat}	base-emitter saturation voltage		-	1	1.2	V
t _d	delay time	V _{CC} = 6 V; I _C = 0.5 A; I _{Bon} = 0.1 A;	-	20	-	ns
r	rise time	I _{Boff} = -0.1 A; T _{amb} = 25 °C	-	280	-	ns
on	turn-on time		-	300	-	ns
·s	storage time		-	2165	-	ns
t _f	fall time		-	275	-	ns
off	turn-off time		-	2440	-	ns
fт	transition frequency	V_{CE} = 10 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	-	33	-	MHz
C _c	collector capacitance	V_{CB} = 20 V; I_{E} = 10 mA; I_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	17	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = 0 \text{ A}; i_c = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	500	-	pF

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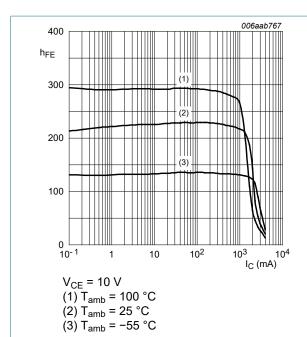


Fig. 4. DC current gain as a function of collector current; typical values

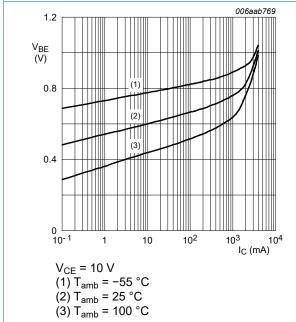


Fig. 6. Base-emitter voltage as a function of collector current; typical values

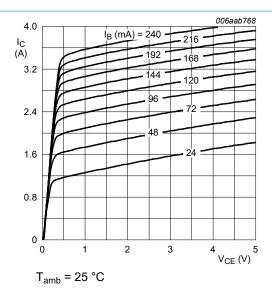
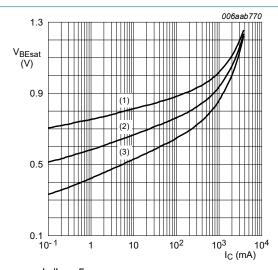


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 5$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$

 $(3) T_{amb} = 100 °C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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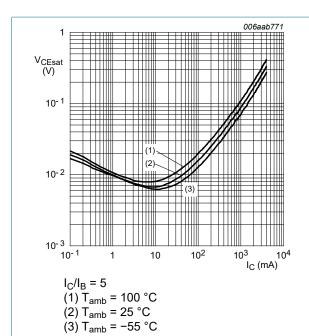


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

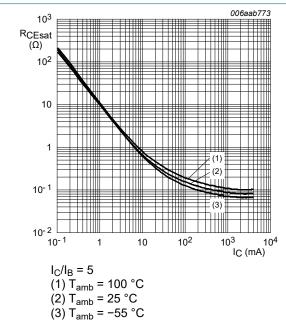


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

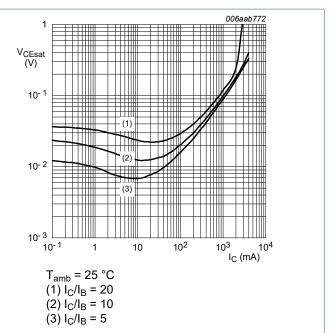


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

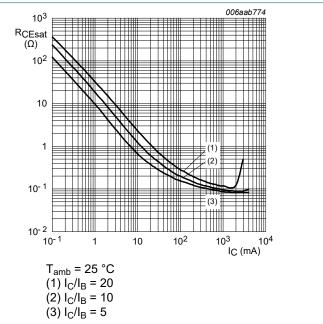
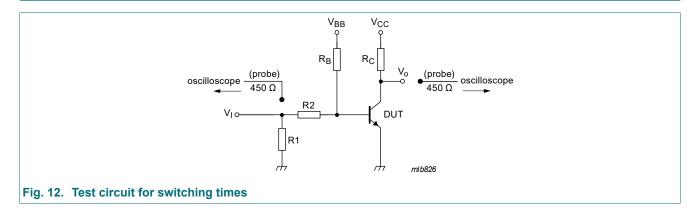


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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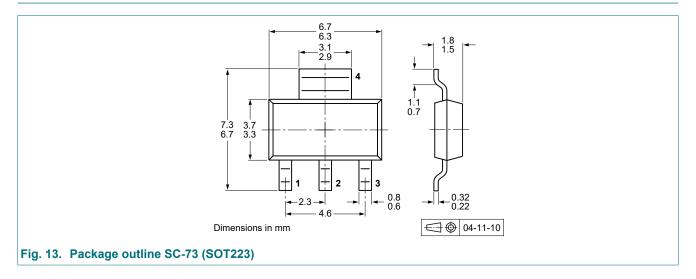
11. Test information



Quality information

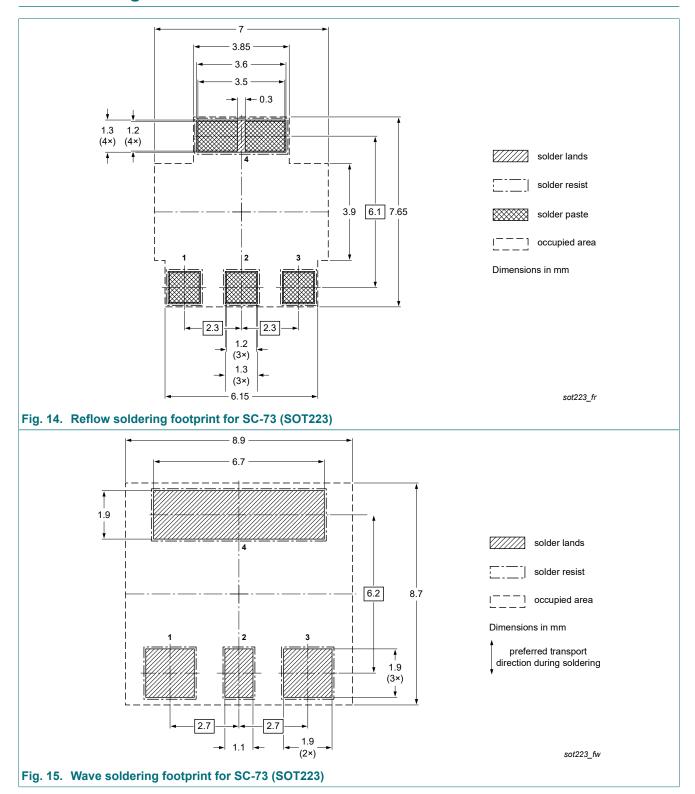
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8215Z-Q v.1	20230712	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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